



P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|---|--------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (A) | | | |
| - 30 | $0.048 \text{ at V}_{GS} = -10 \text{ V}$ | - 5.3 | | | |
| | 0.079 at V _{GS} = - 4.5 V | - 4.1 | | | |

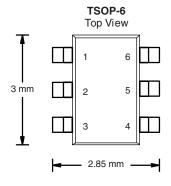
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



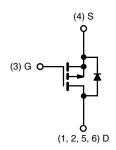
APPLICATIONS

· Load Switch



Ordering Information: Si3481DV-T1-E3 (Lead (Pb)-free)

Si3481DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | | | |
|--|------------------------|-----------------------------------|-------------|--------------|------|--|
| Parameter | | Symbol | 5 s | Steady State | Unit | |
| Drain-Source Voltage | | V _{DS} | - 30 | | ٧ | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | | |
| Continuous Drain Current /T 150 °C\d | T _A = 25 °C | I _D | - 5.3 | - 4.0 | | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | | - 4.2 | - 3.2 | ^ | |
| Pulsed Drain Current | | I _{DM} | - 20 | | Α | |
| Continuous Source Current (Diode Conduction) ^a | | I _S | - 1.7 | - 0.95 | | |
| Mariana Barra Brasilia da | T _A = 25 °C | - P _D | 2.0 | 1.14 | W | |
| Maximum Power Dissipation ^a | T _A = 70 °C | | 1.3 | 0.73 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|---------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Manipania Ingation to Applicati | t ≤ 5 s | - R _{thJA} | 55 | 62.5 | °C/W |
| Maximum Junction-to-Ambient ^a | Steady State | | 90 | 110 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 30 | 36 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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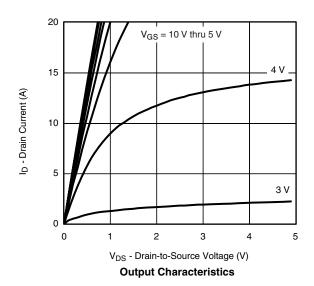
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|---|---------------------|--|-------|--------|-------|------|--|
| Parameter | Symbol | Test Conditions Min. | | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | - 1.0 | | - 3 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zara Cata Valtaga Brain Current | , | V _{DS} = - 30 V, V _{GS} = 0 V | | | - 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 \text{ °C}$ | | | - 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$ | - 20 | | | Α | |
| | В | V _{GS} = - 10 V, I _D = - 5.3 A | | 0.038 | 0.048 | 0 | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 2 A | | 0.063 | 0.079 | ΄9 | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 5.3 A | | 12 | | S | |
| Diode Forward Voltage ^a | V_{SD} | I _S = - 1.7 A, V _{GS} = 0 V | | - 0.85 | - 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | | | 15.5 | 25 | nC | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5.3 \text{ A}$ | | 2.5 | | | |
| Gate-Drain Charge | Q _{gd} | | | 4.3 | | | |
| Turn-On Delay Time | t _{d(on)} | | | 11 | 17 | | |
| Rise Time | t _r | V_{DD} = - 15 V, R_L = 15 Ω | | 14 | 22 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω | | 60 | 90 | ns | |
| Fall Time | t _f | | | 35 | 55 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 1.7 A, dI/dt = 100 A/μs | | 30 | 60 | | |

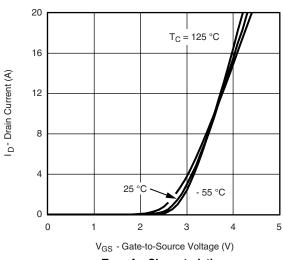
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

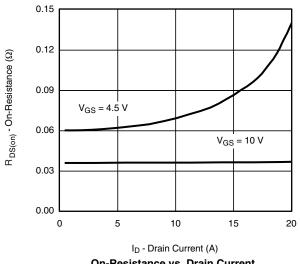


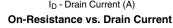


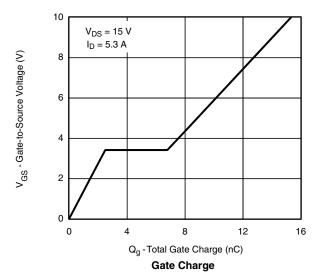


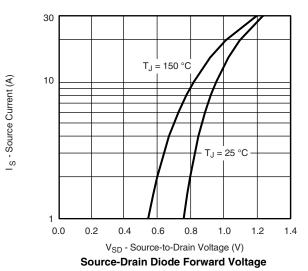


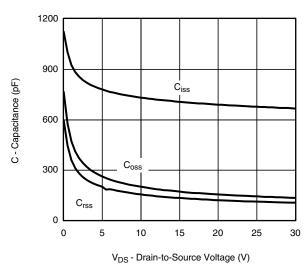
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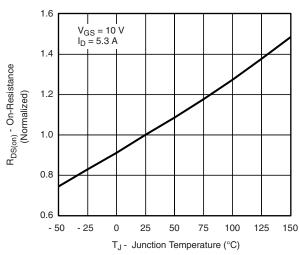




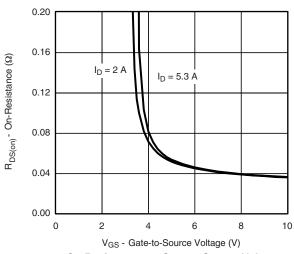




Capacitance



On-Resistance vs. Junction Temperature

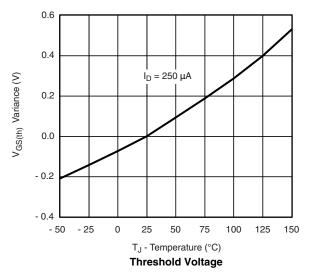


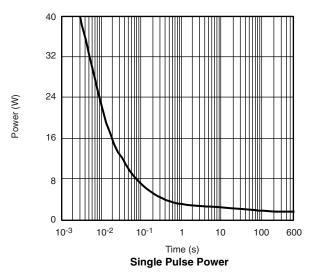
On-Resistance vs. Gate-to-Source Voltage

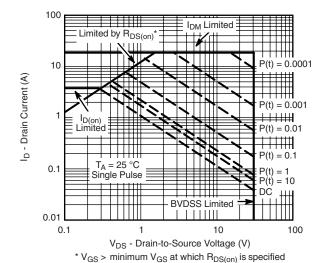
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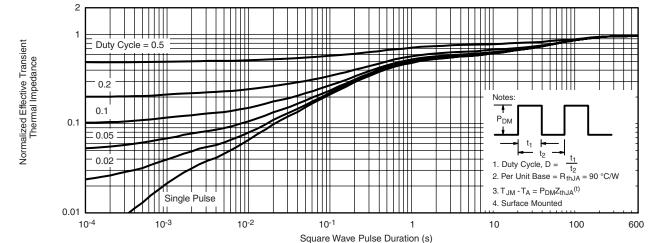
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







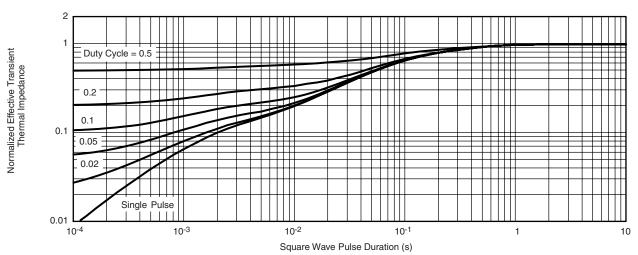
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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